

# HA166152FP4

## Pre Amplifier for Hard Disk Drive

# HITACHI

Rev. 0  
Oct. 1993

The HA166152FP4 is read/write amplifier designed for use with thin film recording heads. They have the following functions and features.

### Functions

- Read amplifier circuit
- Write driver circuit
- Constant write current setup circuit
- 4 channel servo write

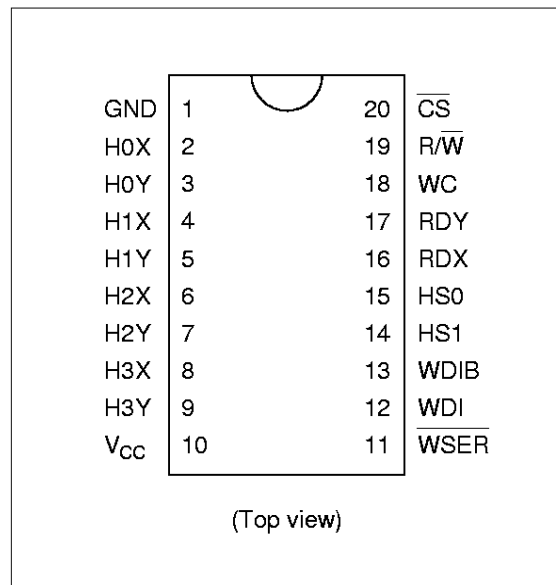
### Features

- Single power supply +5 V
- Low power
  - Read: 195 mW (Typ)
  - Idle: 35 mW (Typ)
- Low Noise: 0.5 nV/ $\sqrt{\text{Hz}}$  (Typ)
- Read amplifier has high differential voltage gain : 345 V/V (Typ)
- Built-in current and voltage monitors
- ECL compatible interface
- Emitter-follower read amplifier outputs
- Input capacitance: 10 pF (Typ)
- Write current range: 5 to 30 mA

### Ordering Information

Type	Channel	Package
HA166152FP4	4	FP-20DA

### Pin Arrangement



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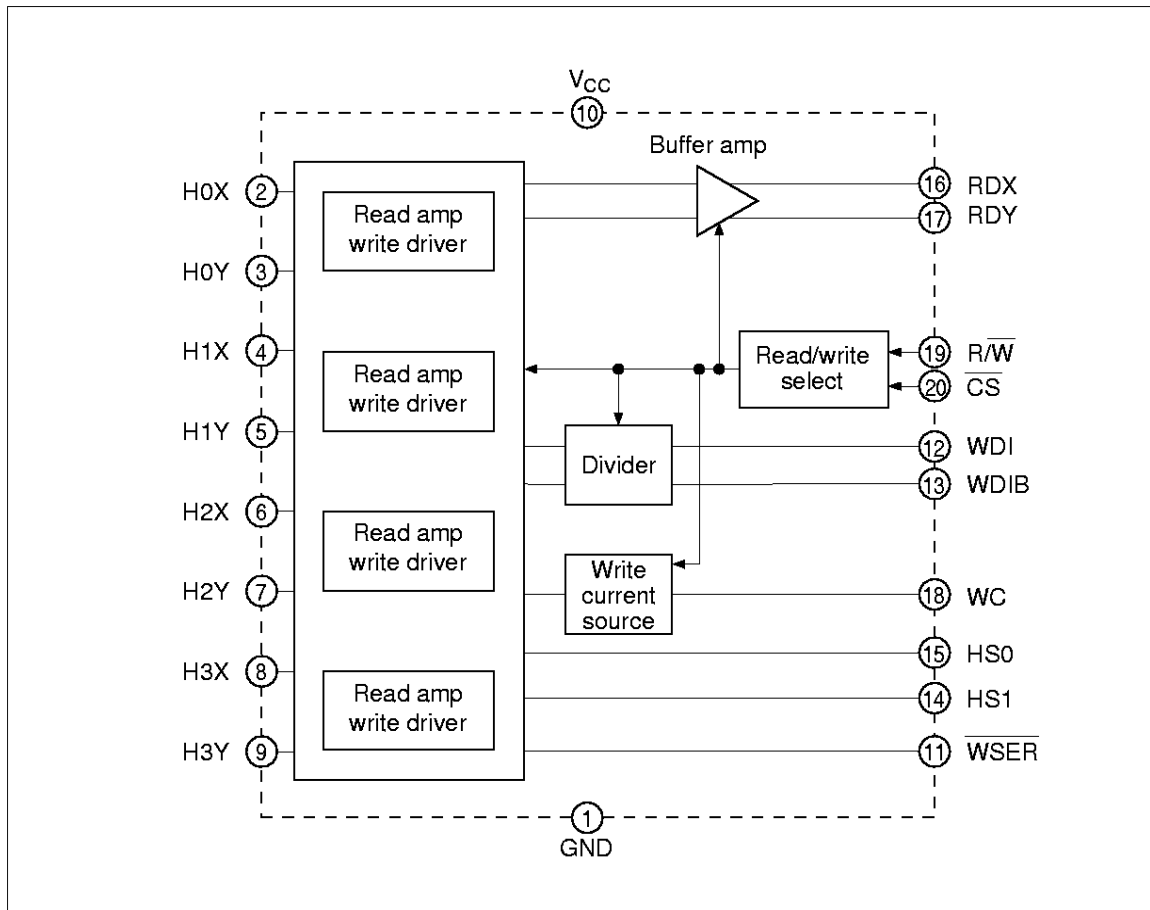
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### Pin Description

Pin No.	Symbol	Pin Name	Description
1	GND	Ground	Ground pins
2, 3	H0X, H0Y	Head 0X, 0Y	These pins are connected to the $\overline{R/W}$ head coil of channel 0.
4, 5	H1X, H1Y	Head 1X, 1Y	These pins are connected to the $\overline{R/W}$ head coil of channel 1.
6, 7	H2X, H2Y	Head 2X, 2Y	These pins are connected to the $\overline{R/W}$ head coil of channel 2.
8, 9	H3X, H3Y	Head 3X, 3Y	These pins are connected to the $\overline{R/W}$ head coil of channel 3.
10	V <sub>CC</sub>	5 V	5 V power supply
11	$\overline{WSER}$	Servo write switch	When $\overline{R/W}$ and $\overline{WSER}$ are set low, all write drivers are selected. Refer to the Mode Select Table.
12, 13	WDI, WDIB	Write data input	Write data input pin. The signal is divided in the IC, and drives the write driver.
14 15	HS1 HS0	Head select 1 Head select 0	Input pins for head select signals. The combination of these signals selects one head from head 0 to head 3. Refer to the head select table.
16, 17	RDX, RDY	Read amplifier output	Differential output pins for the read amp. The signal read out from the head coil is amplified and provided on these pins.
18	WC	Write current setting	Write current setting pin. The write current is defined by the equation below by connecting the external resistance $R_{WC}$ between this pin and GND. Write current [mA] = $K/R_{WC}$ [k $\Omega$ ]
19	$\overline{R/W}$	$\overline{R/W}$ switch	Mode select switch for changing over the bias condition of the head coil  A low level selects the write mode, while a high level selects the read mode.
20	$\overline{CS}$	Chip select	When this line is set high, the circuit goes into the idle state, a low power state. When this line is low, the chip is active.

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**Block Diagram**



**Absolute Maximum Ratings (T<sub>a</sub> = 25°C)**

Item	Symbol	Rating	Unit	Applicable Terminal
Supply voltage	V <sub>CC</sub>	-0.3 to +6.0	V	V <sub>CC</sub>
Write current	I <sub>W</sub>	35	mA	
Interface input voltage	V <sub>IN</sub>	-0.3 to V <sub>CC</sub> +0.3	V	HS0, HS1, WDI, WDIB WSER, R/W, CS
Read data output current	I <sub>RO</sub>	-10	mA	RDX, RDY
Operating temperature	T <sub>opr</sub>	0 to +70	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	
Head voltage swing	V <sub>HSW</sub>	4.0	V <sub>pp</sub>	
Power dissipation	P <sub>T</sub>	550	mW	

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### Power Supply (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	4.5	—	5.5	V	
+5.5 V supply current	I <sub>CC</sub>	—	39	52	mA	Read mode
		—	35 + I <sub>W</sub>	43 + I <sub>W</sub>		Write mode
		—	7	11		Idle mode

### Electrical Characteristics (V<sub>CC</sub> = 5 V, Ta = 25°C unless otherwise specified)

#### Digital Input

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Low level input voltage1	V <sub>IL1</sub>	-0.3	—	0.8	V	
Low level input current1	I <sub>IL1</sub>	-100	—	—	μA	V <sub>IL</sub> = 0.4 V
High level input voltage1	V <sub>IH1</sub>	2.0	—	V <sub>CC</sub> + 0.3	V	
High level input current1	I <sub>IH1</sub>	—	—	20	μA	V <sub>IH</sub> = 2.0 V
Low level input voltage2	V <sub>IL2</sub>	V <sub>CC</sub> - 2	—	V <sub>CC</sub> - 1.65	V	(WDI, WDIB)
Low level input current2	I <sub>IL2</sub>	—	—	0.75	mA	V <sub>IL</sub> = 3.2 V (WDI, WDIB)
High level input voltage2	V <sub>IH2</sub>	V <sub>CC</sub> - 1	—	V <sub>CC</sub> + 0.3	V	(WDI, WDIB)
High level input current2	I <sub>IH2</sub>	—	—	0.95	mA	V <sub>IH</sub> = 4.2 V (WDI, WDIB)
Read/write transition time	t <sub>RW</sub>	—	—	150	ns	
Write/read transition time	t <sub>WR</sub>	—	—	500	ns	
Head select switching delay time	t <sub>HS</sub>	—	—	1000	ns	Read mode
Chip disable transition time	t <sub>IRW</sub>	—	—	1000	ns	Idle to read

Head Select Table

HS1	HS0	Head Selected
L	L	0
	H	1
H	L	2
	H	3

Mode Select Table

R/W	WSER	Mode
L	L	Servo Write*1
	H	Write
H	L	Prohibition
	H	Read

Note: 1. When R/W and WSER are set from high to low, R/W and WSER must be switched at same timing and HS0, HS1 must be set high level.

Read Amplifier

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Differential voltage gain	A <sub>vd</sub>	300	345	390	V/V	f = 300 kHz
Bandwidth	B <sub>w</sub>	(90)*1	(150)*1	—	MHz	-3 dB
Input noise voltage	V <sub>n</sub>	—	(0.5)*1	(0.6)*1	nV/√Hz	f ≤ 15 MHz, Inputs shorted
Common mode rejection ratio	CMRR	60	80	—	dB	
Power supply stability	PSRR	45	60	—		V <sub>CC</sub> ±100 mVp-p, f = 5 MHz
Channel separation	Sep	60	80	—		V <sub>in</sub> = 100 mVp-p on unselected channels and V <sub>in</sub> = 0 mVp-p on selected channels, f = 5 MHz
Output offset voltage	V <sub>o</sub>	-300	—	300	mV	Inputs shorted
Differential input impedance	R <sub>in</sub>	—	0.72	—	kΩ	f = 300 kHz f = 5 MHz
Common mode output voltage	V <sub>com</sub>	2.0	2.5	3.0	V	
Output source current	I <sub>OSO</sub>	—	-10	—	mA	
Output sink current	I <sub>OSI</sub>	1.5	2.0	—		
Input capacitance	C <sub>IN</sub>	—	(10)*1	(15)*1	pF	

Note: 1. These values are only for design purpose.

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## Write Driver

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Write current setting range	$I_W$	5	—	30	mA	
Head current rise time	$t_{hex}$	—	4	15	ns	Lh = 0 $\mu$ H, Rh = 0 $\Omega$ , 10% to 90% point
Head current switching delay time	$t_{d3}$	—	—	30		Rh = 0 $\Omega$ , Lh = 0 $\mu$ H, from 50% point
Head current switching symmetry	$t_{d4}$	—	—	(1)*1		WDI duty cycle = 50%, rise/fall time = 1 ns
Head current gain	$I_H/I_{WC}$	—	19	—	A/A	Head current/ $I_{WC}$
WC output voltage	$V_{WC}$	—	2.8	—	V	
Write current accuracy1	$I_{H1}$	9.45	10.5	11.55	mA	$R_{WC} = 5 \text{ k}\Omega$
Write current accuracy2	$I_{H2}$	18.0	20.0	22.0	mA	$R_{WC} = 2.5 \text{ k}\Omega$
Write current accuracy3	$I_{H3}$	27.0	30.0	33.0	mA	$R_{WC} = 1.6 \text{ k}\Omega$

- Note: 1. These values are only for design purpose.  
 2. Write current constant : K is determined by the following equation.  

$$K = 54.8 - 0.23 I_W \text{ (mA)}$$

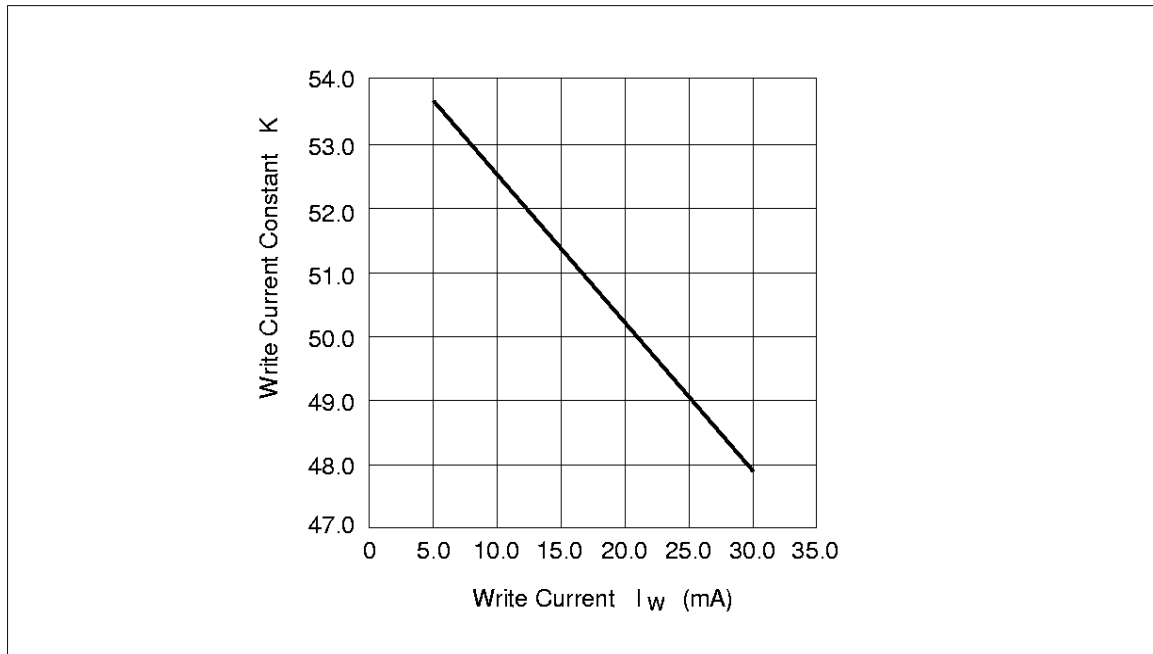
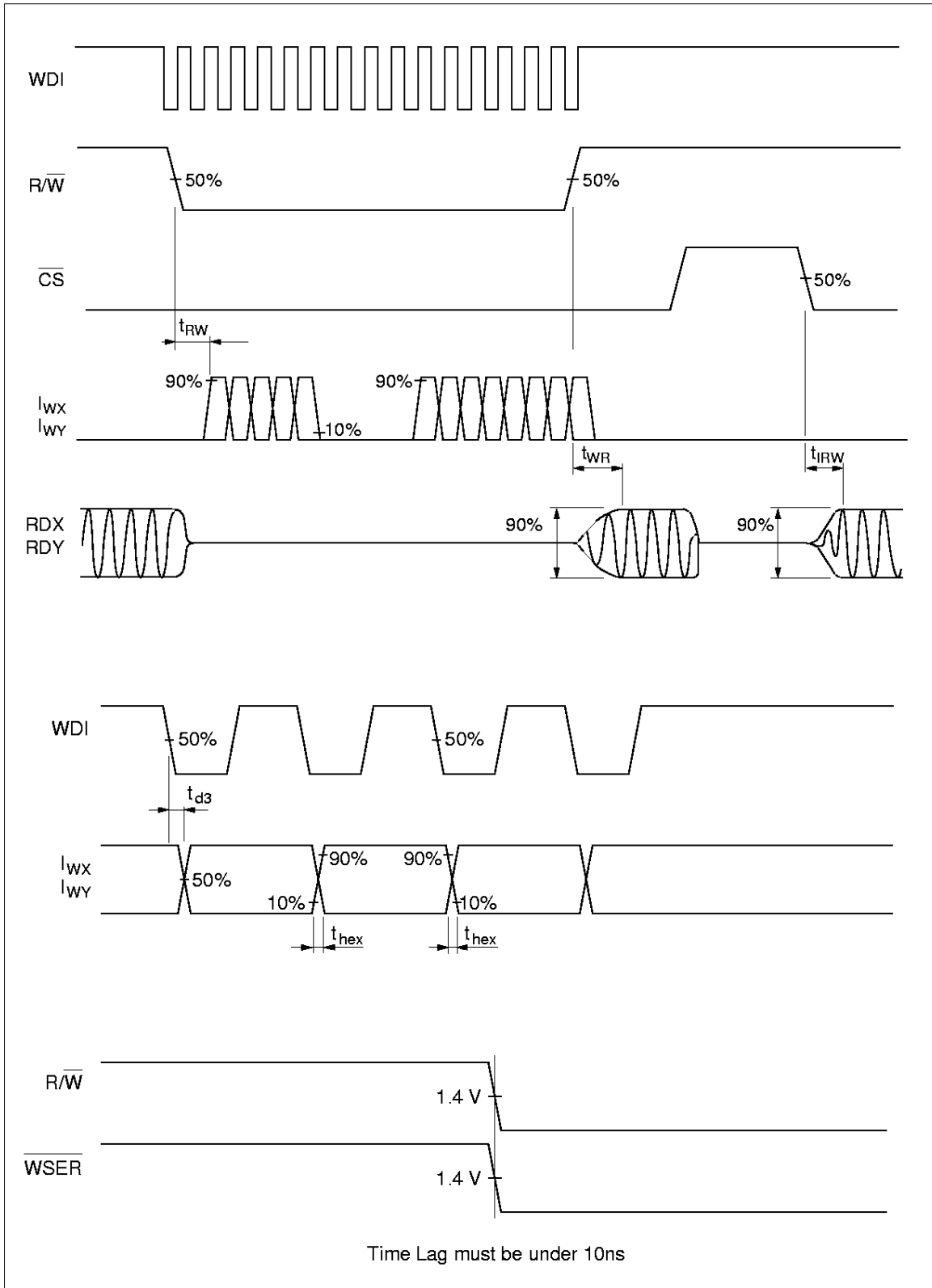


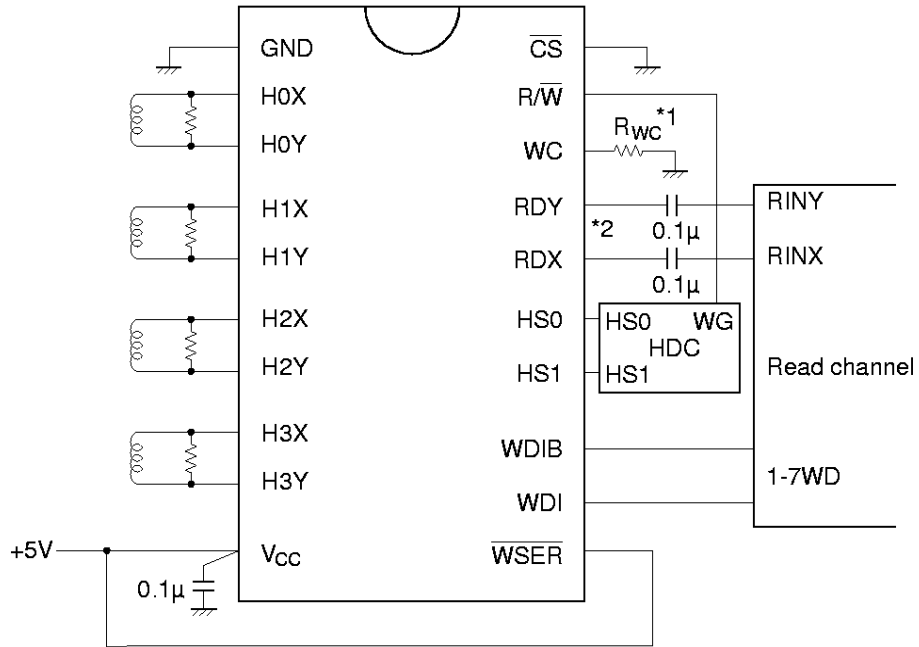
Figure.1 The relation between K and  $I_W$

Timing Waveforms



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## Application Circuit Example



Unit R:  
C: F

Notes: 1. External resistance value  $R_{WC}$  is determined by following equation.

$$R_{WC} [k\Omega] = \frac{K}{\text{Write current [mA]}}$$

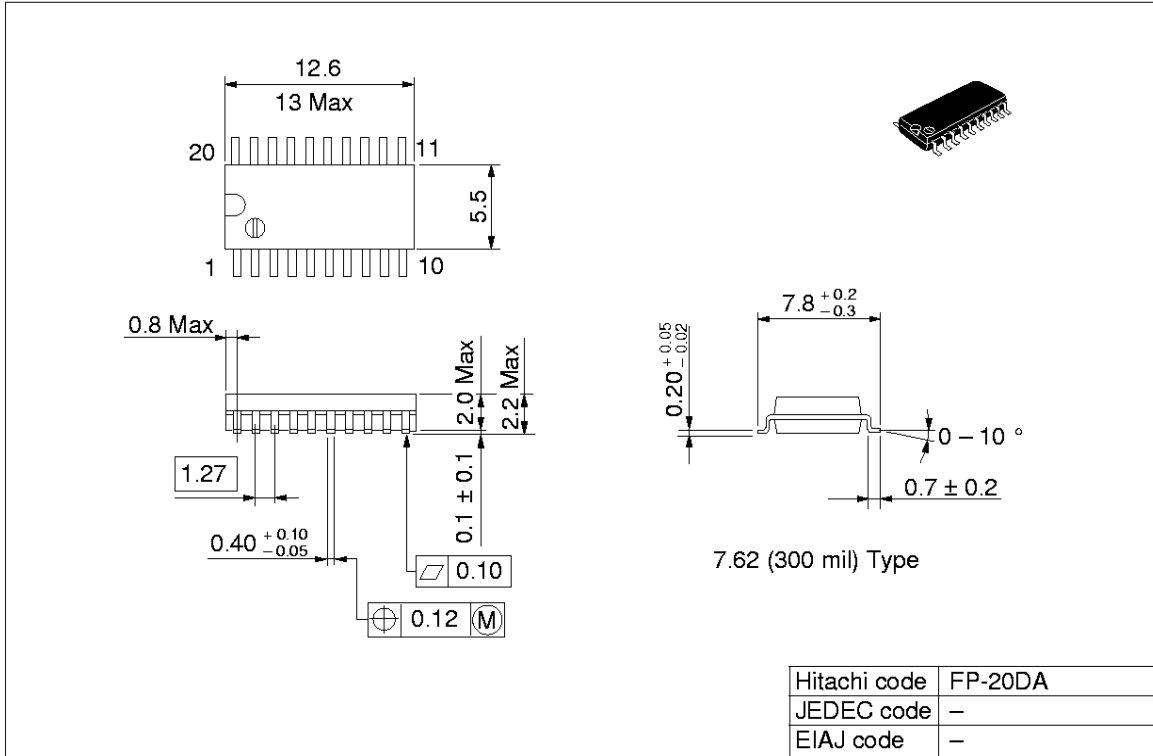
Also, write current ringing on changeover between read and write can be suppressed by locating the resistor  $R_{WC}$  as close as possible to the WC pin.

2. When the length of the wiring pattern increases, the RDX and RDY outputs might have some oscillation. This oscillation can be eliminated by inserting series resistors on these outputs as close to the pins as possible.



Package Dimensions

Unit: mm



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